RECTRON
SEMICONDUCTOR
TECHNICAL SPECIFICATION

FMD1S
THRU
FMD7S

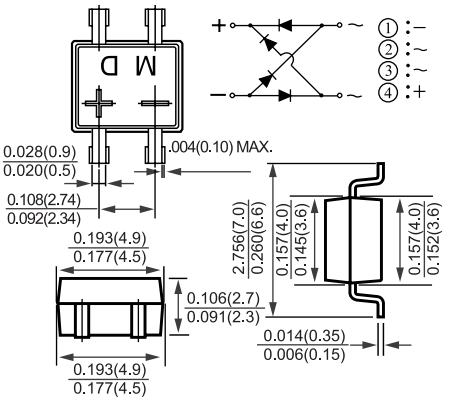
SINGLE-PHASE GLASS PASSIVATED MINI FAST RECOVERY SURFACE MOUNT BRIDGE RECTIFIER

VOLTAGE RANGE 50 to 1000 Volts CURRENT 0.8 Ampere

FEATURES

* Surge overload rating - 30 amperes peak
* Ideal for printed circuit board
* Reliable low cost construction utilizing molded
* Glass passivated device
* Polarity symbols molded on body
* Mounting position: Any
* Weight: 0.5 gram

MD-S



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

MAXIMUM RATINGS (At T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	FMD1S	FMD2S	FMD3S	FMD4S	FMD5S	FMD6S	FMD7S	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Bridge Input Voltage	V_{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Output Rectified Current TA = 30°C -on glass-epoxy P.C.B. (NOTE 1) -on aluminum substrate (NOTE 2)	I_O	0.5 0.8							Amp
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	30							Amps
Typical Junction Capacitance (Note3)	C_J	15							pF
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to + 150							°C

ELECTRICAL CHARACTERISTICS (At T_A = 25°C unless otherwise noted)

CHARACTERISTICS		SYMBOL	FMD1S	FMD2S	FMD3S	FMD4S	FMD5S	FMD6S	FMD7S	UNITS
Maximum Forward Voltage Drop per Bridge Element at 0.4A DC		V_F	1.30							Volts
Maximum Reverse Current at rated DC Blocking Voltage per element	@T_A = 25°C	I_R	10							uAmps
	@T_A = 125°C		100							uAmps
Maximum Reverse Recovery Time (Note 4)		trr	150				250	500		nSec

NOTE: 1. On glass-epoxy P.C.B. mounted on 0.05 X 0.05" (1.3 X 1.3mm) pads.

2. On aluminum substrate P.C.B. with an area of 0.8 X 0.8 X 0.25" (20 X 20 X 6.4mm) mounted on 0.05 X 0.05" (1.27 X 1.27mm) solder pad.

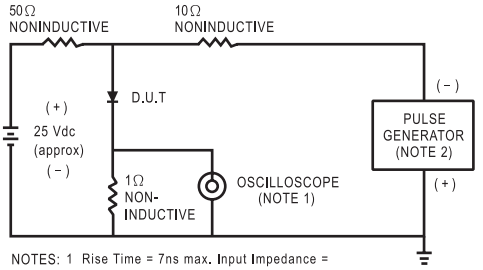
3. Measured at 1MHz and applied reverse voltage of 4.0 volts.

4. Test Conditions: I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A.

5. Suffix "-S" Surface Mount for Mini Dip Bridge.

RATING AND CHARACTERISTIC CURVES (FMD1S THRU FMD7S)

FIG. 1 - TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1 Rise Time = 7ns max. Input Impedance = 1 megohm. 22pF.
2. Rise Time = 10ns max. Source Impedance = 50 ohms.

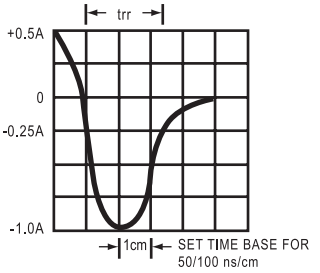


FIG. 1 - TYPICAL FORWARD CURRENT DERATING CURVE

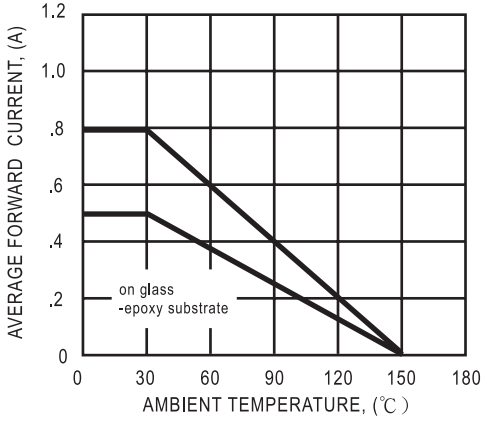


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

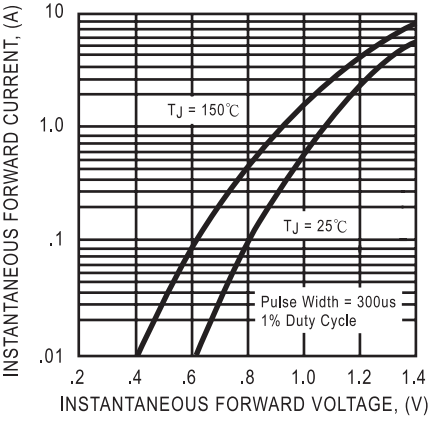


FIG. 4 - TYPICAL JUNCTION CAPACITANCE

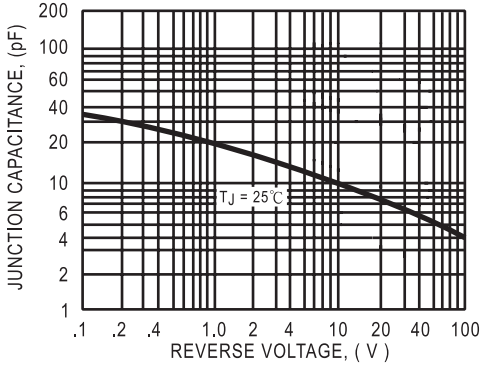


FIG. 3 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT